

**Amendments to the Claims:**

1. (Original) A semiconductor device that includes a semiconductor substrate having a via hole that penetrates the semiconductor substrate from a surface to a reverse side, wherein a part of an electrode formed on the surface of the semiconductor substrate reaches the reverse side of the semiconductor substrate through the via hole, and an inside of the via hole is filled in with a photosensitive resin to fully cover an aperture of the via hole on the surface of the semiconductor substrate.

2. (Original) The semiconductor device according to Claim 1, wherein the photosensitive resin is filled in more shallowly than depth of the via hole.

3. (Original) The semiconductor device according to Claim 2, wherein a main ingredient of the photosensitive resin is silicone resin or epoxy resin.

4. (Original) The semiconductor device according to Claim 3, wherein viscosity of the photosensitive resin at 25°C is 70~600 m Pa·s.

5. (Original) The semiconductor device according to Claim 1, wherein the main ingredient of the photosensitive resin is the silicone resin or the epoxy resin.

6. (Original) The semiconductor device according to Claim 1, wherein viscosity of the photosensitive resin at 25°C is 70~600 m Pa·s.

Claims 7-16 (Cancelled).